Doc No. TT4-EA-14636

Panasonic

Revision. 5

MOS FET

2N7002E

2N7002E

Silicon N-channel MOSFET

For switching circuits
Panasonic parts No. FK360602

■ Features

- Low Drain-source On-state Resistance : RDS(on) typ = 1 Ω (VGS = 4.5 V)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)

■ Marking Symbol : GV

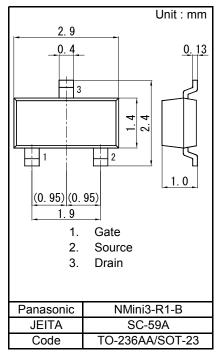
■ Packaging

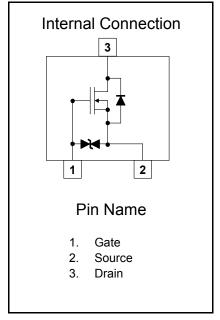
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit	
Drain to Source Voltage	VDS	60	V	
Gate to Source Voltage	VGS	±20	V	
Drain Current	ID	300	mΑ	
Drain Current (Pulsed) *1	IDp	600	mA	
Total Power Dissipation*2	PD	350	mW	
Channel Temperature	Tch	150	°C	
Storage Temperature Range	Tstg	-55 to +150	°C	

Note *1 Pulse test: Ensure that the channel temperature does not exceed 150 $^{\circ}\text{C}$





Established: 2013-04-19 Revised: 2013-10-10

^{*2} Mounted on FR4 board (25.4mm×25.4mm×t0.8mm,Cu area >300mm²)

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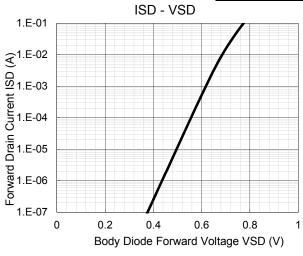
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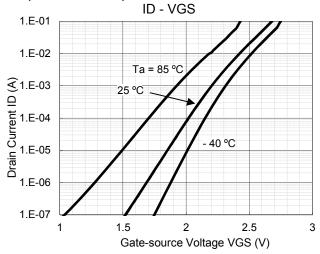
■ Electrical Characteristics Ta = 25 °C ± 3 °C

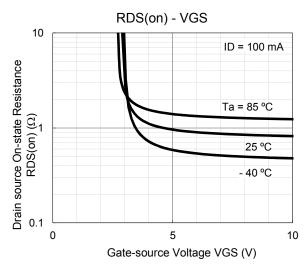
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 250 μA, VGS = 0 V	60			V
Zero Gate Voltage Drain Current	IDSS	VDS = 60 V, VGS = 0 V			1	μΑ
Gate-source Leakage Current	IGSS	VGS = ±20 V, VDS = 0 V			±10	μΑ
Gate-source Threshold Voltage	Vth	ID = 250 μA, VDS = 10 V	1		3	V
Drain-source On-state Resistance	RDS(on)1	ID = 100 mA, VGS = 10 V		8.0	3	Ω
	RDS(on)2	ID = 100 mA, VGS = 4.5 V		1	4	
Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V f = 1 MHz		40		pF
Output Capacitance	Coss			7		
Reverse Transfer Capacitance	Crss	1 - 1 1011 12		4.5		
Total Gate Charge	Qg	VDC = 10 V VCC = 0 to 4 E V		8.0		nC
Gate to Source Charge	Qgs	VDS = 10 V, VGS = 0 to 4.5 V ID = 200 mA		0.2		
Gate to Drain Charge	Qgd	1D - 200 IIIA		0.4		

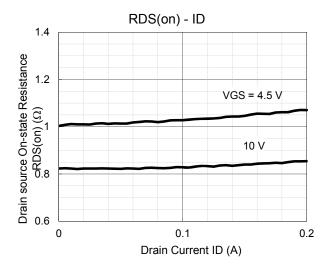
Note: Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

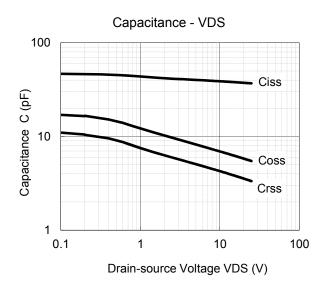


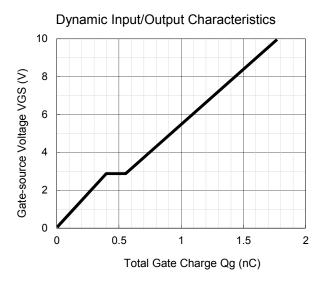






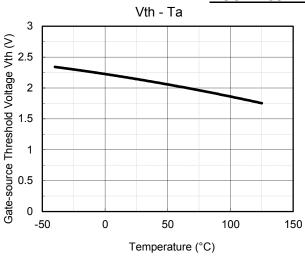


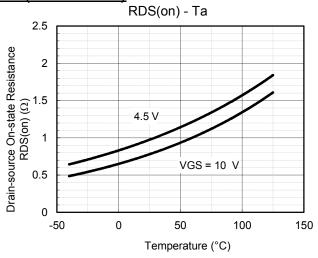




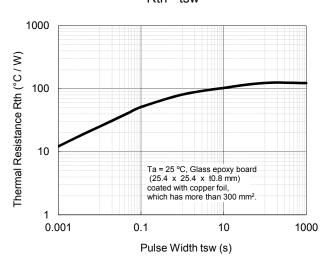
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Technical Data (reference)

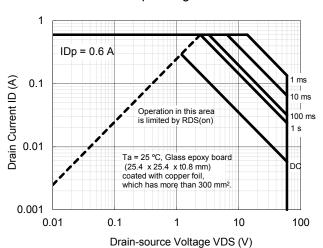


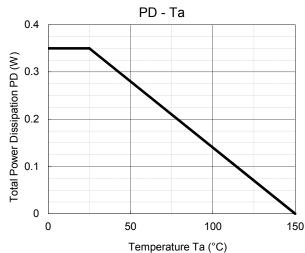


Rth - tsw



Safe Operating Area



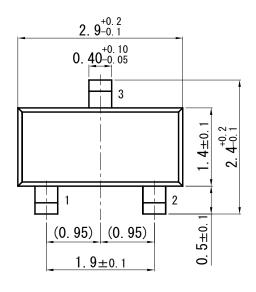


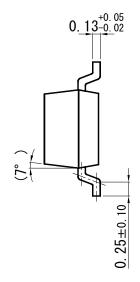
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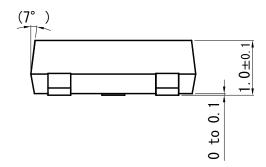
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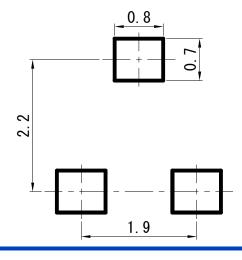
Unit: mm







■ Land Pattern (Reference) (Unit : mm)



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